

SEMICONDUCTOR

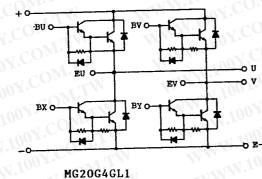
TECHNICAL DATA

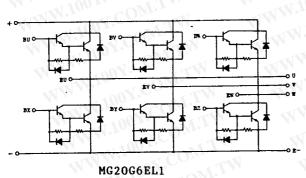
HIGH POWER SWITCHING APPLICATIONS.
MOTOR CONTROL APPLICATIONS.

FEATURES :

- . The Collector is Isolated from Case
- 4 or 6 Darlington Transistors including Free Wheeling Diodes are Built-in to
 1 package
- . High DC Current Gain
 - : $h_{FE} = 100(Min.) (I_{C} = 20A)$
- . Low Satulation Voltage

EQUIVALENT CIRCUIT





90D 16213

DT-33-35

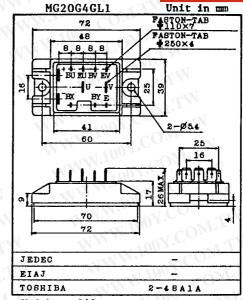
TOSHIBA GTR MODULE

MG20G4GL1 MG20G6EL1

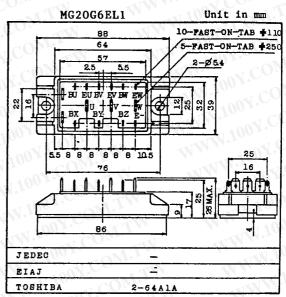
SILICON NPN TRIPLE DIFFU

勝 特 力 材 料 886-3-5753170 胜特力电子(上海) 86-21-34970699 胜特力电子(深圳) 86-755-83298787

Http://www. 100y. com. tw



Weight: 140g



Weight: 180g

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TECHNICAL DATA

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MAXIMUM RATINGS (Ta=25	5°C)	WW	N. 100Y.CO.	1
CHARACTER	CHARACTERISTIC		RATING	רואט
Collector-Base Voltage	Collector-Base Voltage		600	V
Collector-Emitter Sust	Collector-Emitter Sustaining Voltage		600	V
Collector-Emitter Sust	Collector-Emitter Sustaining Voltage		450	V
Emitter-Base Voltage	Emitter-Base Voltage		6 V.Co	V
Collector Current	DC	IC	20 0	A
COTTECTOR CUTTORIE	lms	I _{CP}	40	A
Forward Current	DC	ΙF	20	A
N. C. C. T. W. W.	lms	lms IFM		A
Base Current	Base Current		2	A
Collector Power Dissip	Collector Power Dissipation (Tc=25°C)		125	W
Junction Temperature	Junction Temperature		150	°C
Storage Temperature Ra	Storage Temperature Range		-40 ~ 125	°c
Isolation Voltage	Isolation Voltage		2500 (AC 1 Minute)	CV.
Screw Torque	Screw Torque		30	kg · cm

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	TINU	
ollector Cut-off Current	ICBO	VCB=600V, IE=0	41/	$M_{r_{r}}$	1.0	mА	
mitter Cut-off Current	IEBO	VEB=6V, IC=0	-		100	mA	
ollector-Emitter ustaining Voltage	VCEO(SUS)	I _C =0.5A, L=40mH	450		100 x	\ Cv	
C Current Gain	hFE	V _{CE} =5V, I _C =20A	100	- 	1.100	-1 C(
Collector-Emitter Saturation Voltage	VCE(sat)	I _C =20A, I _B =0.5A	1	M.	2.0	v	
Base-Emitter Saturation Voltage	VBE(sat)	VM:1003COWT	-	W	2.5	v	
Turn-on Time	ton	INPUT OUTFUT	1 -	-4	1.0	1100	
witching Time Storage Time	tstg	50.4s C	W -	-	12	μs.	
Fall Time	tf	DUTY - 182=C2 Y	LA	-	2.0	TWA	
orward Voltage	VF	I _F =20A, I _B =0	<u> 7-7</u> //	-	1.6	V.	
Reverse Recovery Time	trr	IF=20A, V _{BE} =-2V di/dt=60A/µs	V.TY		0.7	μS	
Thermal Resistance	Rth(j-c)	W 100 - CC	N.T.	-T	1.0	°C/W	

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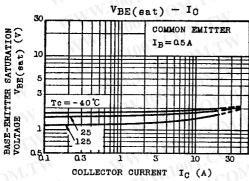


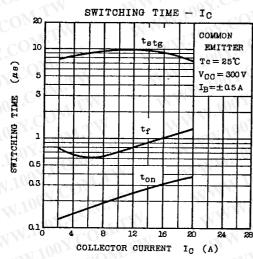
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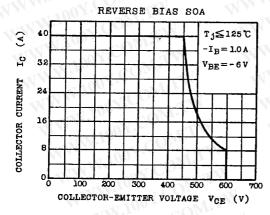
TECHNICAL DATA

90D 16215 DT-33-35

M G 2 O G 4 G L 1 M G 2 O G 6 E L 1

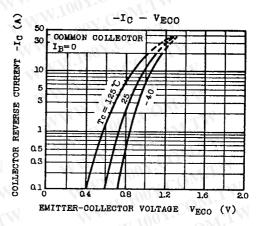




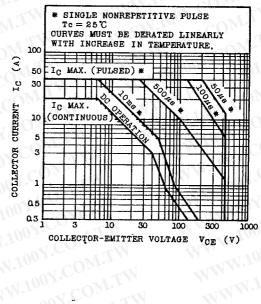


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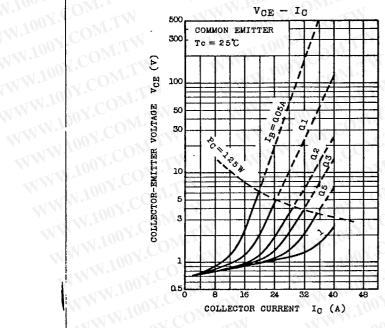
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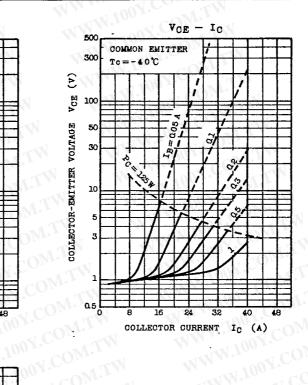
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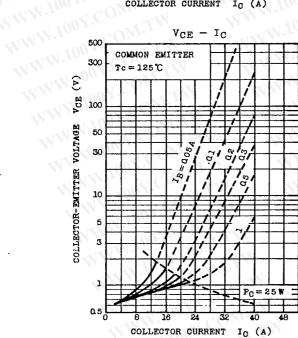


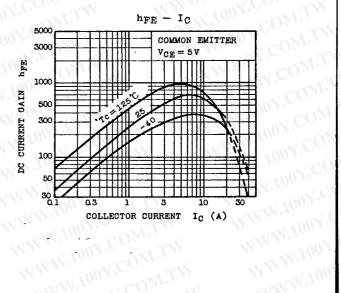


MG20G4GL1









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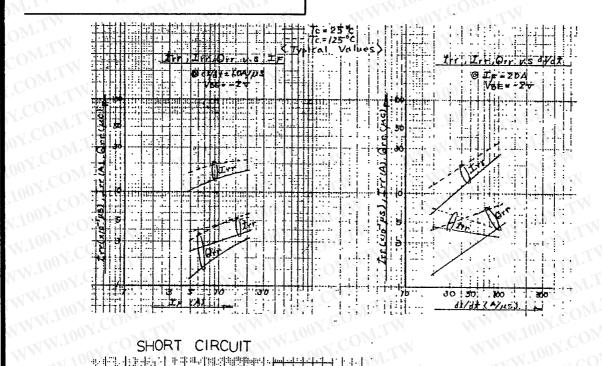
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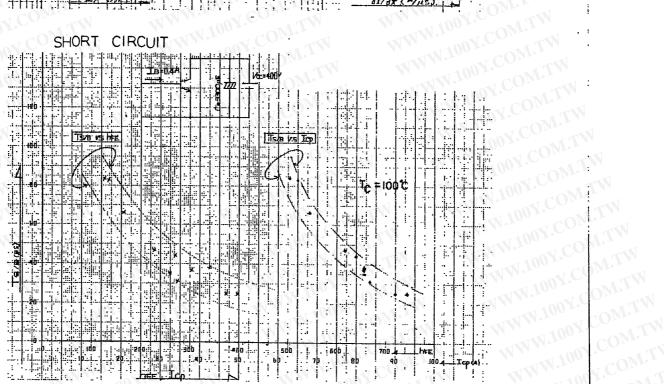
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TECHNICAL DATA

MG20G4GLI MG20G6ELI







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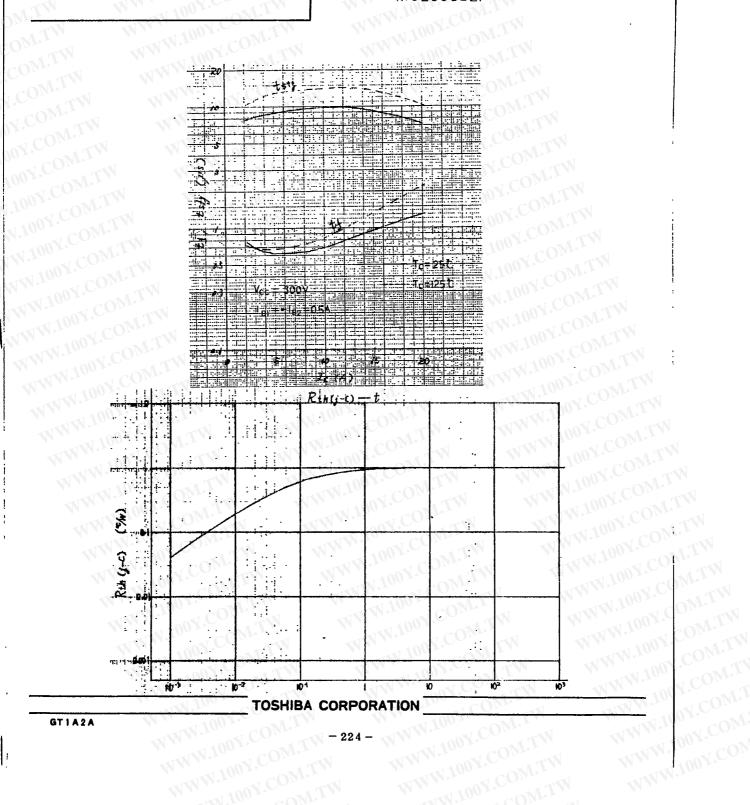
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